

Title (en)
METHOD OF PASSIVATING SEMICONDUCTOR ELEMENTS BY APPLYING A SILICON LAYER

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Abstract (en)
[origin: CA1111149A] The present invention relates to a process for passivating the surfaces of semiconductor elements. Silicon layers which are vapourdeposited on the surface of semiconductor elements have the effect of a permanent stability on the characteristic curves of the semiconductor element. These silicon layers are annealed, in order to reduce the inverse currents. This effects a permanent lowering of the inverse-current level. This invention may be used on all semiconductor elements.

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